

**AMENDMENTS TO CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A deep trench structure of semiconductor device, said semiconductor device having a plurality of active areas, said deep trench structure ~~characterized in that said having a deep trench communicates communicating with two different active areas which are respectively connected to two adjacent bit lines.~~
2. (Currently Amended) The structure as claimed in Claim 1, wherein the cross section of said deep trench communicates with said two different active areas.
3. (Canceled)
4. (Currently Amended) A semiconductor memory device comprising:
  - a plurality of bit lines;
  - a plurality of gates crossing intersecting with said bit lines;
  - a plurality of active areas, each of which is connected to one of said bit lines;
  - a plurality of deep trenches, at least one of which communicates with two different active areas which are respectively connected with adjacent two of said bit lines.
5. (Currently Amended) The device as claimed in Claim 4, wherein the cross section of said deep trench communicates with said two different active areas.
6. (Canceled)